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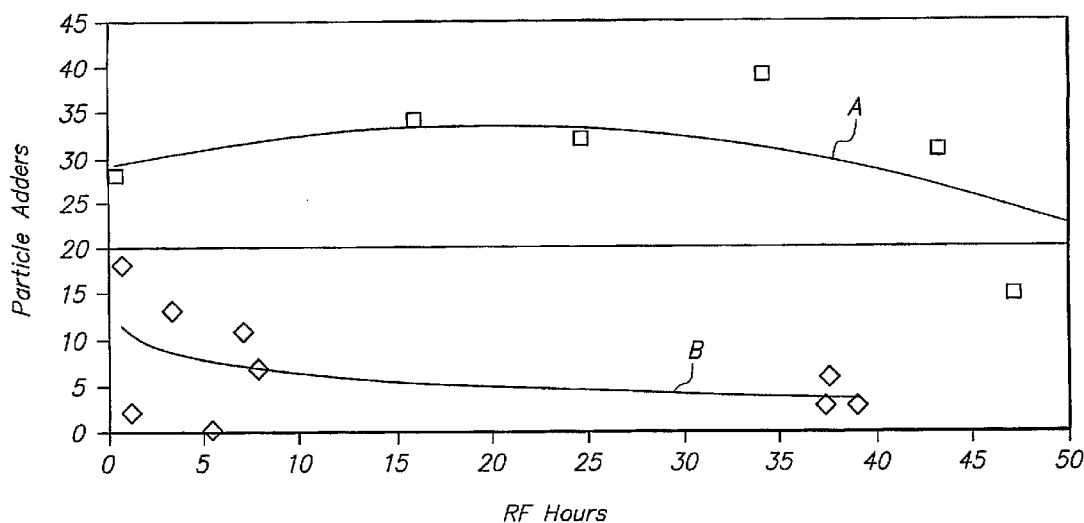
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(54) Title: SILICON CARBIDE COMPONENTS OF SEMICONDUCTOR SUBSTRATE PROCESSING APPARATUSES TREATED TO REMOVE FREE-CARBON



(57) Abstract: Silicon carbide components of a plasma processing apparatus, methods of making the components, and methods of using the components during processing of semiconductor substrates to provide for reduced particle contamination of the substrates are provided. The silicon carbide components are made by a process that results in free-carbon in the components. The silicon carbide components are treated to remove the free-carbon from at least the surface.